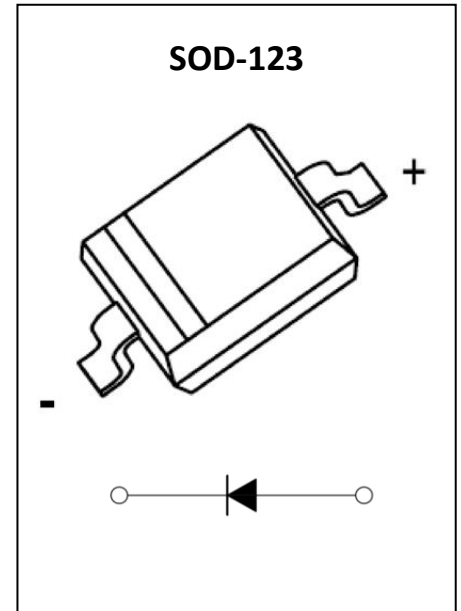


**RB160M-60 Schottky Barrier Diode**

**Feature**

- Small Power Mold Type
- Low IR
- Low VF
- High Reliability

**MARKING:**



**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

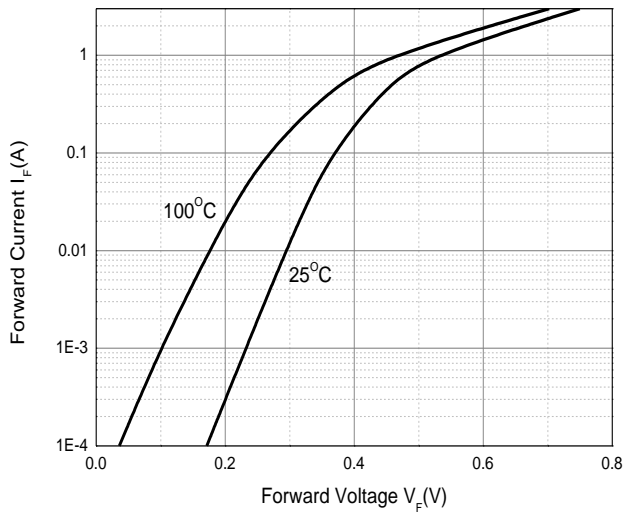
Parameter	Symbol	Value	Unit
DC reverse voltage	V <sub>R</sub>	60	V
Mean rectifying current	I <sub>O</sub>	1	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I <sub>FSM</sub>	25	A
Power Dissipation	P <sub>D</sub>	0.35	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	285	°C/W
Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

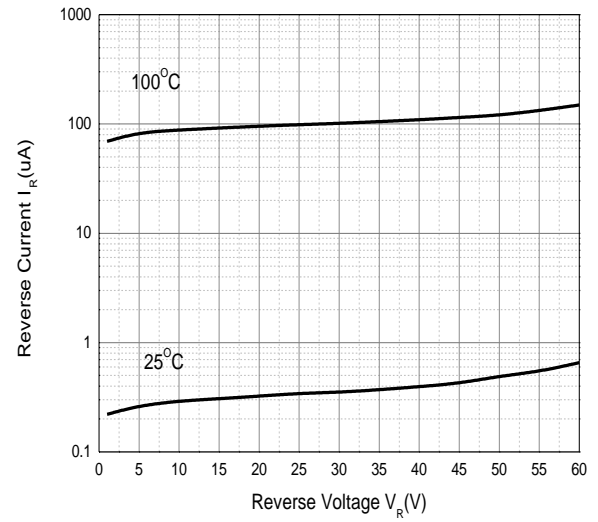
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V <sub>BR</sub>	I <sub>R</sub> =250μA	60	70	-	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =0.5A	0	0.44	0.49	V
		I <sub>F</sub> =1.0A	0	0.51	0.55	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =60V	-	1	8	μA
Capacitance between terminals	C <sub>t</sub>	V <sub>R</sub> =10V, f=1MHZ	-	50	-	pF

**Typical Characteristics**

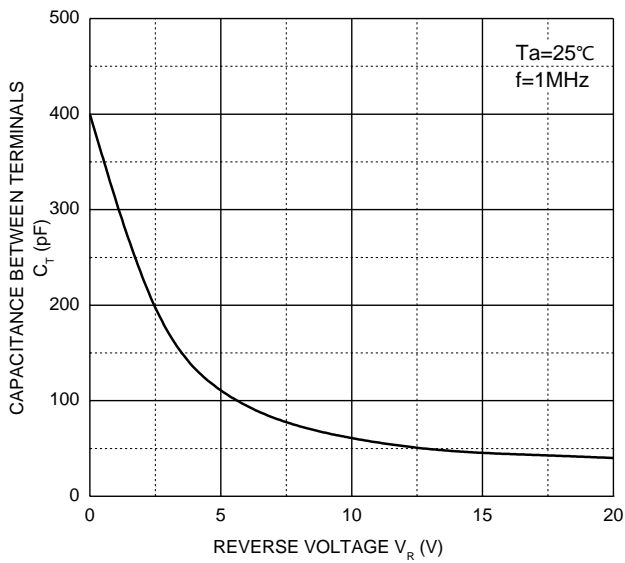
Forward Characteristics



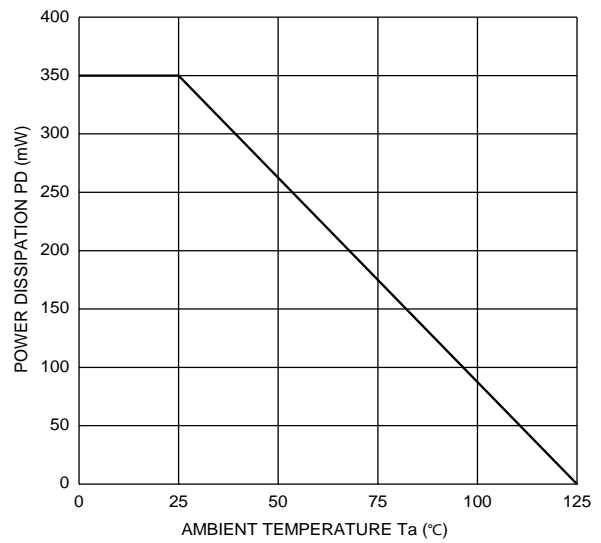
Reverse Characteristics

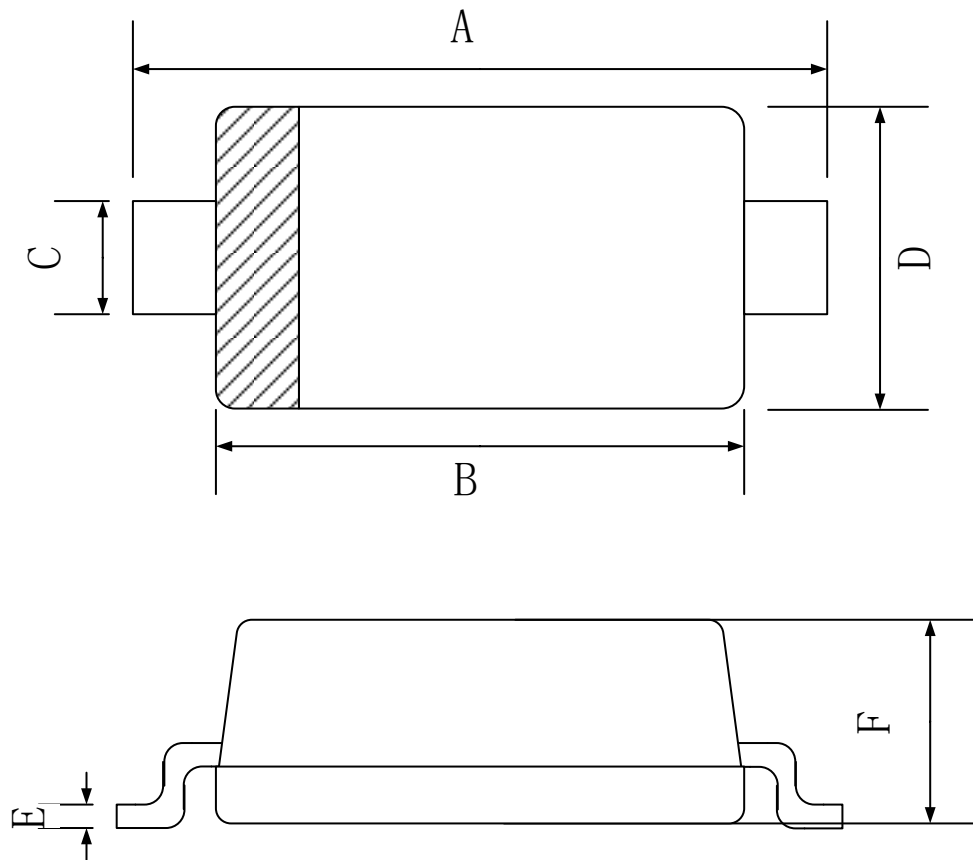


Capacitance Characteristics



Power Derating Curve



**SOD-123 Package Outline Dimensions**


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	3.45	3.65	3.85
B	2.55	2.65	2.75
C	0.45	0.55	0.65
D	1.50	1.60	1.70
E	0.09	0.105	0.12
F	0.95	1.15	1.35

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)